

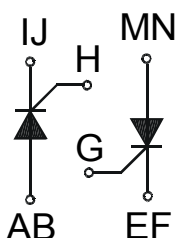
Single Phase AC Controller Modules

PSW1C100

$I_{TRMS} = 96 \text{ A}$
 $V_{RRM} = 600-1600 \text{ V}$

Preliminary Data Sheet

V_{RSM} V_{DSM} (V)	V_{RRM} V_{DRM} (V)	Type
700	600	PSW1C 100/06
900	800	PSW1C 100/08
1300	1200	PSW1C 100/12
1500	1400	PSW1C 100/14
1700	1600	PSW1C 100/16



Symbol	Test Conditions	Maximum Ratings	Features
I_{TRMS}	$T_{VJ} = T_{VJM}$	96 A	<ul style="list-style-type: none"> • Thyristor controller for AC (circuit W1C acc. to IEC) for mains frequency □ • Isolation voltage 3000 V~ • Planar glass passivated chips • Low forward voltage drop • Leads suitable for PC board soldering • UL registered, E 148688
I_{TAVM}	$T_C = 75 \text{ °C}; 180^\circ \text{ sine}$	63 A	
I_{TAVM}	$T_C = 85 \text{ °C}; 180^\circ \text{ sine}$	53 A	
I_{TSM}	$T_{VJ} = 45 \text{ °C}$ t = 10 ms (50 Hz), sine	1200 A	
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	1300 A	
	$T_{VJ} = 125 \text{ °C}$ t = 10 ms (50 Hz), sine	1100 A	
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	1200 A	
$\int i^2 dt$	$T_{VJ} = 45 \text{ °C}$ t = 10 ms (50 Hz), sine	7200 A ² s	
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	7000 A ² s	
	$T_{VJ} = 125 \text{ °C}$ t = 10 ms (50 Hz), sine	6050 A ² s	
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	5970 A ² s	
$(di/dt)_{cr}$	$T_{VJ} = 125 \text{ °C}$ repetitive, $I_T = 150 \text{ A}$ f=50Hz, $t_p=200\mu s$	150 A/ μs	
	$V_D=2/3V_{DRM}$ $I_G=0.45 \text{ A}$ non repetitive, $I_T = I_{TAVM}$ $di_G/dt=0.45A/\mu s$	500 A/ μs	
	$(dv/dt)_{cr}$ $T_{VJ} = 125 \text{ °C}$ $V_D=2/3V_{DRM}$ $R_{GK} = \infty$, method 1 (linear voltage rise)	1000 V/ μs	
P_{GM}	$T_{VJ} = 125 \text{ °C}$ $t_p=30\mu s$	≤ 10 W	
	$I_T = I_{TAVM}$ $t_p=300\mu s$	≤ 5 W	
P_{GAVM}		0.5 W	
V_{RGM}		10 V	
T_{VJ}		-40... + 125 °C	
T_{VJM}		125 °C	
T_{stg}		-40... + 125 °C	
V_{ISOL}	50/60 Hz, RMS t = 1 min	2500 V~	
	$I_{ISOL} \leq 1 \text{ mA}$ t = 1 s	3000 V~	
M_d	Mounting torque (M4)	1.5 - 1.8 Nm	
		14 - 16 lb.in.	
Weight	typ.	18 g	

Data according to IEC 60747 refer to a single thyristor unless otherwise stated

Symbol	Test Conditions	Characteristic Value
$I_{D,R}$	$T_{VJ} = 125^{\circ}\text{C}$, $V_R = V_{RRM}$, $V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 200$ A, $T_{VJ} = 25^{\circ}\text{C}$	≤ 1.55 V
V_{TO}	For power-loss calculations only	0.85 V
r_T		4.0 m Ω
V_{GT}	$V_D = 6$ V, $T_{VJ} = 25^{\circ}\text{C}$	≤ 1.5 V
	$T_{VJ} = -40^{\circ}\text{C}$	≤ 1.6 V
I_{GT}	$V_D = 6$ V, $T_{VJ} = 25^{\circ}\text{C}$	≤ 100 mA
	$T_{VJ} = -40^{\circ}\text{C}$	≤ 200 mA
V_{GD}	$T_{VJ} = 125^{\circ}\text{C}$, $V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = 125^{\circ}\text{C}$, $V_D = 2/3 V_{DRM}$	≤ 10 mA
I_L	$T_{VJ} = 25^{\circ}\text{C}$, $t_p = 10\mu\text{s}$, $V_D = 6$ V $I_G = 0.45$ A, $di_G/dt = 0.45$ A/ μs	≤ 450 mA
I_H	$T_{VJ} = 25^{\circ}\text{C}$, $V_D = 6$ V, $R_{GK} = \infty$	≤ 200 mA
t_{gd}	$T_{VJ} = 25^{\circ}\text{C}$, $V_D = 1/2 V_{DRM}$ $I_G = 0.45$ A, $di_G/dt = 0.45$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = T_{VJM}$, $I_T = 120$ A; $t_p = 200\mu\text{s}$; $di/dt = 10$ A/ μs typ. 150	μs
	$V_R = 100$ V; $dv/dt = 20$ V/ μs ; $V_D = 2/3 V_{DRM}$	
R_{thJC}	per thyristor; DC	0.53 K/W
	per module	0.27 K/W
R_{thJK}	per thyristor; sine 180° el	typ. 0.73 K/W
	per module	typ. 0.37 K/W
d_s	Creeping distance on surface	6.6 mm
d_A	Creeping distance in air	9.7 mm
a	Max. allowable acceleration	50 m/s ²

Package style and outline

Dimensions in mm (1mm = 0.0394")

